

Thyristor \ Diode Module

$$V_{RRM} = 2 \times 800 \text{ V}$$

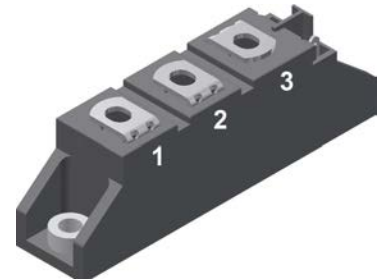
$$I_{TAV} = 116 \text{ A}$$

$$V_T = 1,28 \text{ V}$$

Phase leg

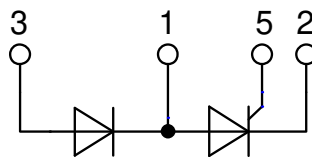
Part number

MCD95-08io8B



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

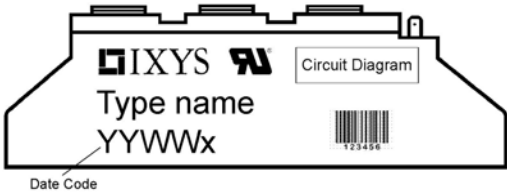
Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.



Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$				900	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$				800	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 800\text{ V}$	$T_{VJ} = 25^{\circ}C$			200	μA
		$V_{R/D} = 800\text{ V}$	$T_{VJ} = 125^{\circ}C$			5	mA
V_T	forward voltage drop	$I_T = 150\text{ A}$	$T_{VJ} = 25^{\circ}C$			1,29	V
		$I_T = 300\text{ A}$				1,50	V
		$I_T = 150\text{ A}$	$T_{VJ} = 125^{\circ}C$			1,28	V
		$I_T = 300\text{ A}$				1,70	V
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 125^{\circ}C$			116	A
$I_{T(RMS)}$	RMS forward current	180° sine				182	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}C$			0,85	V
r_T	slope resistance					2,4	m Ω
R_{thJC}	thermal resistance junction to case					0,22	K/W
R_{thCH}	thermal resistance case to heatsink				0,2		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$			455	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$			2,25	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2,43	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}C$			1,92	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2,07	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$			25,3	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			24,6	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}C$			18,3	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			17,7	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}C$		119		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu s$	$T_C = 125^{\circ}C$			10	W
		$t_p = 300\text{ }\mu s$				5	W
P_{GAV}	average gate power dissipation					0,5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C; f = 50\text{ Hz}$ repetitive, $I_T = 250\text{ A}$				150	A/ μs
		$t_p = 200\text{ }\mu s; di_G/dt = 0,45\text{ A}/\mu s;$ $I_G = 0,45\text{ A}; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 116\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 125^{\circ}C$			1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}C$			2,5	V
			$T_{VJ} = -40^{\circ}C$			2,6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}C$			150	mA
			$T_{VJ} = -40^{\circ}C$			200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$			0,2	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_p = 10\text{ }\mu s$	$T_{VJ} = 25^{\circ}C$			450	mA
		$I_G = 0,45\text{ A}; di_G/dt = 0,45\text{ A}/\mu s$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$			200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$			2	μs
		$I_G = 0,45\text{ A}; di_G/dt = 0,45\text{ A}/\mu s$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 150\text{ A}; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10\text{ A}/\mu s; dv/dt = 20\text{ V}/\mu s; t_p = 200\text{ }\mu s$	$T_{VJ} = 100^{\circ}C$		185		μs

Package TO-240AA				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				200	A
T _{VJ}	virtual junction temperature			-40		125	°C
T _{op}	operation temperature			-40		100	°C
T _{stg}	storage temperature			-40		125	°C
Weight					81		g
M _D	mounting torque			2,5		4	Nm
M _T	terminal torque			2,5		4	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	13,0	9,7			mm
d _{Spb/Apb}		terminal to backside	16,0	16,0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		4800		V
		t = 1 minute			4000		V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD95-08io8B	MCD95-08io8B	Box	36	453307

Similar Part	Package	Voltage class
MCMA110PD1200TB	TO-240AA-1B	1200
MCMA140PD1200TB	TO-240AA-1B	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 125^{\circ}\text{C}$



Thyristor

$V_{0\text{ max}}$

$R_{0\text{ max}}$

threshold voltage

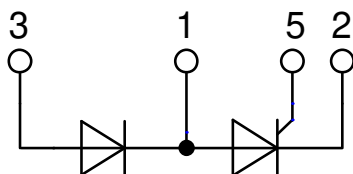
*slope resistance **

0,85

1,2

V

mΩ



Thyristor

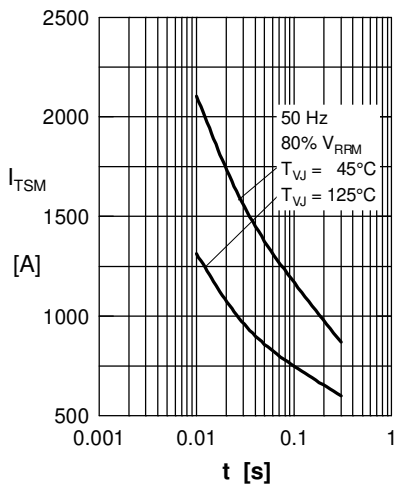


Fig. 1 Surge overload current I_{TSM} ,
 I_{FSM} : Crest value, t : duration

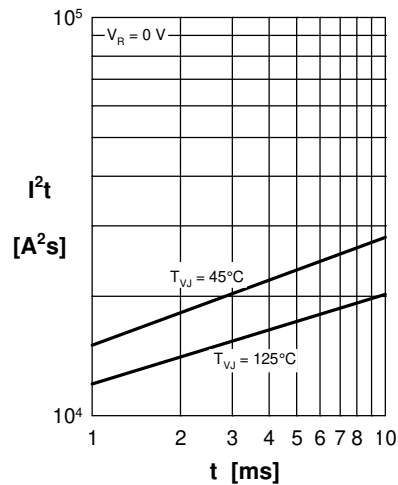


Fig. 2 I^2t versus time (1-10 ms)

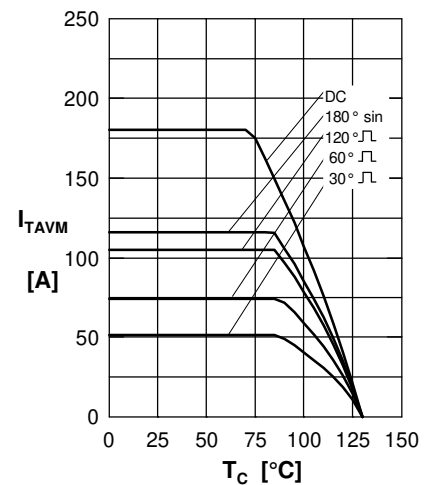


Fig. 3 Max. forward current
 at case temperature

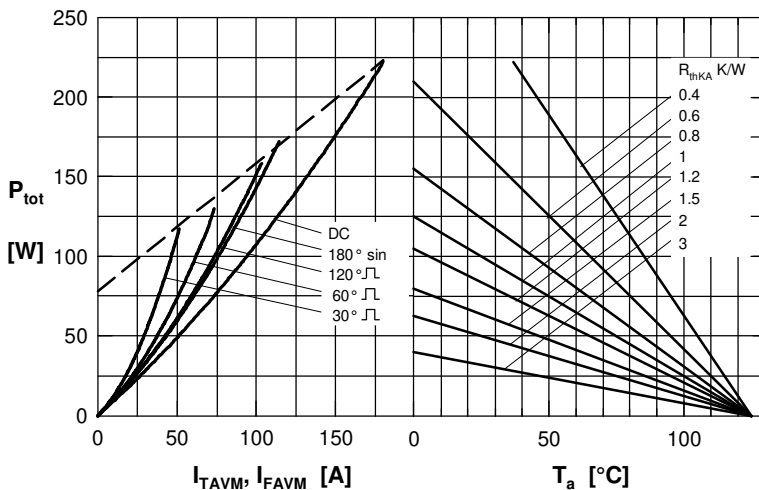


Fig. 4 Power dissipation vs. on-state current & ambient temperature
 (per thyristor or diode)

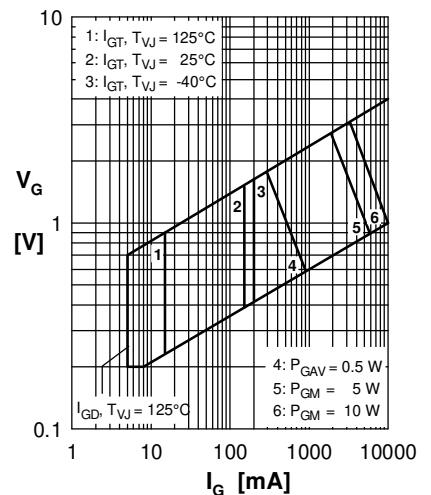


Fig. 5 Gate trigger characteristics

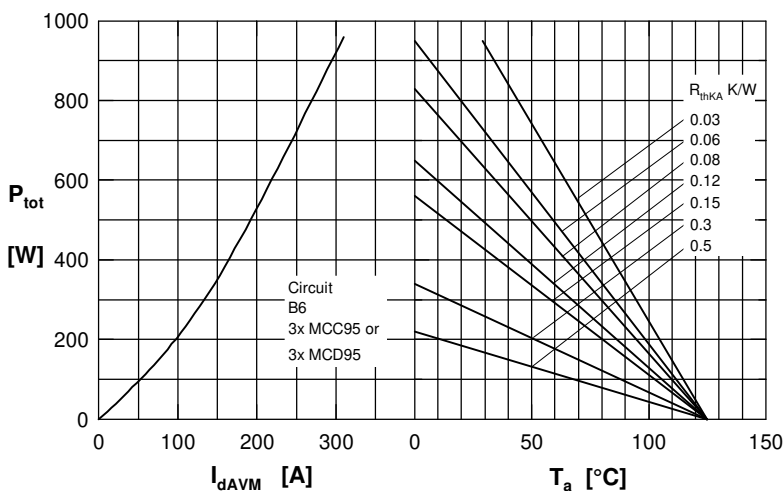


Fig. 6 Three phase rectifier bridge: Power dissipation vs. direct
 output current and ambient temperature

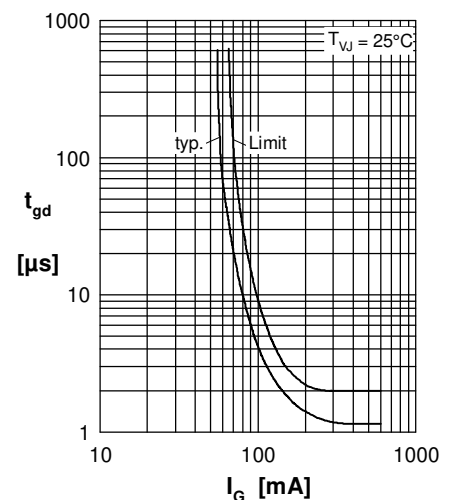


Fig. 7 Gate controlled delay time

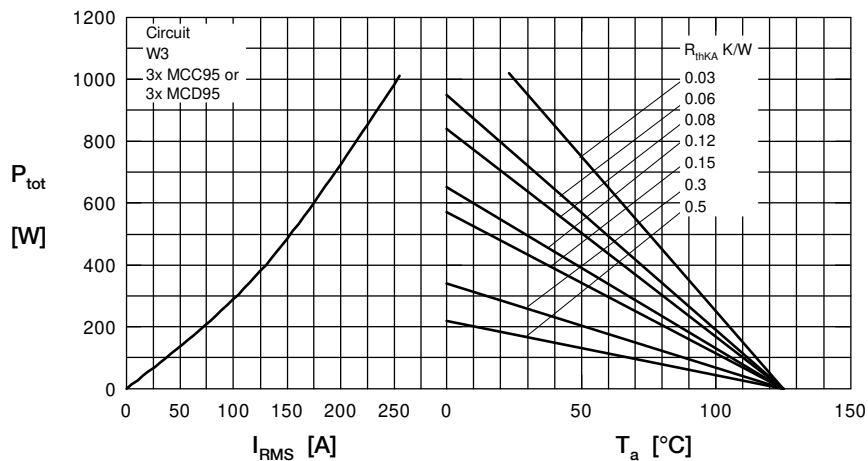
Rectifier


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

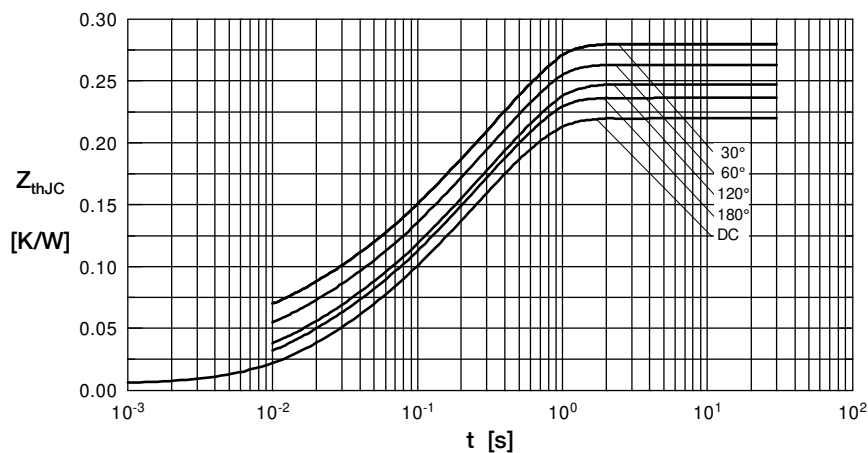


Fig. 9 Transient thermal impedance junction to case (per thyristor/diode)

$R_{\theta JC}$ for various conduction angles d:

d	$R_{\theta JC}$ [K/W]
DC	0.22
180°	0.23
120°	0.25
60°	0.27
30°	0.28

Constants for Z_{thJC} calculation:

i	$R_{\theta i}$ [K/W]	t_i [s]
1	0.0066	0.0019
2	0.0678	0.0477
3	0.1456	0.3440

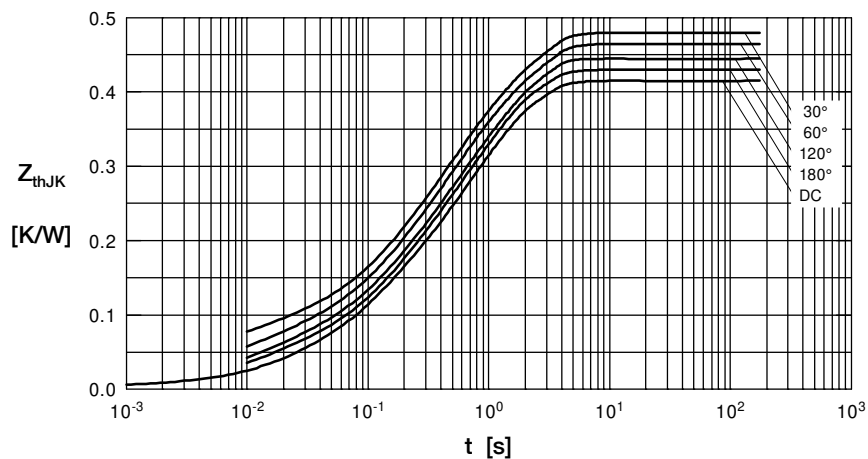


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)

$R_{\theta JK}$ for various conduction angles d:

d	$R_{\theta JK}$ [K/W]
DC	0.42
180°	0.43
120°	0.45
60°	0.47
30°	0.48

Constants for Z_{thJK} calculation:

i	$R_{\theta i}$ [K/W]	t_i [s]
1	0.0066	0.0019
2	0.0678	0.0477
3	0.1456	0.3440
4	0.2000	1.3200